

# HYS64T128020HM-3.7-A HYS64T128020HM-5-A

214-Pin Micro-DIMM-DDR2-SDRAM Modules

MDIMM

DDR2 SDRAM

RoHS Compliant

Memory Products



N e v e r   s t o p   t h i n k i n g .

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Never stop thinking.

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All	Only green products included	
<b>19</b>	IDD current defined	
<b>26</b>	SPD Codes added	
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## 214-Pin Micro-DIMM-DDR2-SDRAM Modules MDIMM

HYS64T128020HM-3.7-A  
HYS64T128020HM-5-A

# 1 Overview

This chapter gives an overview of the 214-Pin Micro-DIMM-DDR2-SDRAM Modules product family and describes its main characteristics.

## 1.1 Features

- 214-Pin PC2-4200 and PC2-3200 DDR2 SDRAM memory modules for use as main memory when installed in systems such as mobile personal computers.
- 128M × 64 module organisation and 64M × 16 chip organisation
- JEDEC standard Double-Data-Rate-Two Synchronous DRAMs (DDR2 SDRAM) with a single + 1.8 V (± 0.1 V) power supply
- Built with 1 Gb DDR2 SDRAMs in P-TFBGA-92 chipsize packages
- Programmable CAS Latencies (3, 4 and 5), Burst Length (8 & 4) and Burst Type
- Burst Refresh, Distributed Refresh and Self Refresh
- All inputs and outputs SSTL\_1.8 compatible
- OCD (Off-Chip Driver Impedance Adjustment) and ODT (On-Die Termination)
- Serial Presence Detect with E<sup>2</sup>PROM
- Micro-DIMM Dimensions (nominal) : 30 mm high, 54.0 mm wide
- Based on JEDEC standard reference layouts Raw Card "B"
- 2-piece type Mezzanine Socket with 0,4 mm contact centers
- RoHS Compliant Products<sup>1)</sup>

**Table 1 Performance**

Product Type Speed Code			-3.7	-5	Units
Speed Grade			PC2-4200 4-4-4	PC2-3200 3-3-3	—
max. Clock Frequency	@CL5	$f_{CK5}$	266	200	MHz
	@CL4	$f_{CK4}$	266	200	MHz
	@CL3	$f_{CK3}$	200	200	MHz
min. RAS-CAS-Delay		$t_{RCD}$	15	15	ns
min. Row Precharge Time		$t_{RP}$	15	15	ns
min. Row Active Time		$t_{RAS}$	45	40	ns
min. Row Cycle Time		$t_{RC}$	60	55	ns

1) RoHS Compliant Product: Restriction of the use of certain hazardous substances (RoHS) in electrical and electronic equipment as defined in the directive 2002/95/EC issued by the European Parliament and of the Council of 27 January 2003. These substances include mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls and polybrominated biphenyl ethers.

## 1.2 Description

The INFINEON HYS64T128020HM-[3.7/5]-A module family are low profile Unbuffered Micro-DIMM modules “MDIMMs” with 30,0 mm height based on DDR2 technology. DIMMs are available as 128M × 64 organisation and density, intended for mounting into 214-pin mezzanine connector sockets.

The memory array is designed with 1 Gb Double-Data-Rate-Two (DDR2) Synchronous DRAMs. Decoupling capacitors are mounted on the PCB board. The DIMMs feature serial presence detect based on a serial E<sup>2</sup>PROM device using the 2-pin I<sup>2</sup>C protocol. The first 128 bytes are programmed with configuration data and are write protected; the second 128 bytes are available to the customer.

**Table 2 Ordering Information**



Product Type <sup>1)</sup>	Compliance Code <sup>2)</sup>	Description	SDRAM Technology
HYS64T128020HM-3.7-A	1GB 2R×16 PC2-4200M-444-11-A0	two ranks 1 GByte DIMM	1 Gbit (×16)
HYS64T128020HM-5-A	1GB 2R×16 PC2-4200M-444-11-A0	two ranks 1 GByte DIMM	1 Gbit (×16)

- 1) All part numbers end with a place code, designating the silicon die revision. Example: HYS64T128020HM-3.7-A, indicating Rev. “A” dies are used for DDR2 SDRAM components. For all INFINEON DDR2 module and component nomenclature see [Chapter 7](#) of this data sheet.
- 2) The Compliance Code is printed on the module label and describes the speed grade, e.g. “PC2-4200M-444-11-A0”, where 4200M means Micro-DIMM modules with 4.26 GB/sec Module Bandwidth and “444-11” means Column Address Strobe (CAS) latency = 4, Row Column Delay (RCD) latency = 4 and Row Precharge (RP) latency = 4 using the latest JEDEC SPD Revision 1.1 and produced on the Raw Card “A”.

**Table 3 Address Format**

DIMM Density	Module Organization	Memory Ranks	# of SDRAMs	# of row/bank/column bits	Raw Card
1 GByte	128M × 64	2	8	13/3/10	A

**Table 4 Components on Modules<sup>1)</sup>**

Product Type <sup>2)</sup>	DRAM Components <sup>2)</sup>	DRAM Density	DRAM Organisation
HYS64T128020HM-3.7-A	HYB18T1G160AF	1 Gbit	64M × 16
HYS64T128020HM-5-A	HYB18T1G160AF	1 Gbit	64M × 16

- 1) For a detailed description of all functionalities of the DRAM components on these modules see the component data sheet.
- 2) Green Product

## 2 Pin Configuration

The pin configuration of the DDR2 SDRAM Micro-DIMM is listed by function in [Table 5](#) (214 pins). The abbreviations used in columns Pin and Buffer Type are explained in [Table 6](#) and [Table 7](#) respectively. The pin numbering is depicted in [Figure 1](#).

**Table 5 Pin Configuration of MDIMM**

Pin#	Name	Pin Type	Buffer Type	Function
<b>Clock Signals</b>				
122	CK0	I	SSTL	<b>Clock Signals CK 1:0, Complement Clock Signals <math>\overline{CK}</math> 1:0</b> <i>Note: The system clock inputs. All address and command lines are sampled on the cross point of the rising edge of CK and the falling edge of <math>\overline{CK}</math>. A Delay Locked Loop (DLL) circuit is driven from the clock inputs and output timing for read operations is synchronized to the input clock.</i>
194	CK1	I	SSTL	
123	$\overline{CK0}$	I	SSTL	
195	$\overline{CK1}$	I	SSTL	
<b>Clock Enables 1:0</b>				
43	CKE0	I	SSTL	<i>Note: Activates the DDR2 SDRAM CK signal when HIGH and deactivates the CK signal when LOW. By deactivating the clocks, CKE0 initiates the Power Down Mode or the Self Refresh Mode.</i>  <i>Note: 2-rank module</i>
147	CKE1	I	SSTL	
	NC	NC		
<b>Control Signals</b>				
165	$\overline{S0}$	I	SSTL	<b>Chip Select Rank 1:0</b> <i>Note: Enables the associated DDR2 SDRAM command decoder when LOW and disables the command decoder when HIGH. When the command decoder is disabled, new commands are ignored but previous operations continue. Rank 0 is selected by <math>\overline{S0}</math>; Rank 1 is selected by <math>\overline{S1}</math>. The input signals also disable all outputs (except CKE and ODT) of the register(d) on the DIMM when both inputs are high. When <math>\overline{S}</math> is HIGH, all register outputs (except CK, ODT and Chip select) remain in the previous state.</i>  <i>Note: 2-rank module</i>
62	$\overline{S1}$	I	SSTL	
	NC	NC		
163	$\overline{RAS}$	I	SSTL	<b>Row Address Strobe (RAS), Column Address Strobe (CAS), Write Enable (WE)</b> <i>Note: When sampled at the cross point of the rising edge of CK, and falling edge of <math>\overline{CK}</math>, <math>\overline{RAS}</math>, <math>\overline{CAS}</math> and <math>\overline{WE}</math> define the operation to be executed by the SDRAM.</i>
60	$\overline{CAS}$	I	SSTL	
56	$\overline{WE}$	I	SSTL	
<b>Address Signals</b>				
55	BA0	I	SSTL	<b>Bank Address Bus 1:0</b>
162	BA1	I	SSTL	<i>Note: Select internal SDRAM memory bank</i>



**Table 5 Pin Configuration of MDIMM (cont'd)**

Pin#	Name	Pin Type	Buffer Type	Function
46	BA2	I	SSTL	<b>Bank Address Bus 2</b> <i>Note: greater than 512Mb DDR2 SDRAMS</i>
	NC	NC	–	<i>Note: less than 1Gb DDR2 SDRAMS</i>
161	A0	I	SSTL	<b>Address Inputs 12:0, Address Input 10/Autoprecharge</b> <i>Note: During a Bank Activate command cycle, defines the row address when sampled at the crosspoint of the rising edge of CK and falling edge of <math>\overline{CK}</math>. During a Read or Write command cycle, defines the column address when sampled at the cross point of the rising edge of CK and falling edge of <math>\overline{CK}</math>. In addition to the column address, AP is used to invoke autoprecharge operation at the end of the burst read or write cycle. If AP is HIGH, autoprecharge is selected and BA[2:0] defines the bank to be precharged. If AP is LOW, autoprecharge is disabled. During a Precharge command cycle, AP is used in conjunction with BA[2:0] to control which bank(s) to precharge. If AP is HIGH, all banks will be precharged regardless of the state of BA[2:0] inputs. If AP is LOW, then BA[2:0] are used to define which bank to precharge.</i>
159	A1	I	SSTL	
52	A2	I	SSTL	
158	A3	I	SSTL	
51	A4	I	SSTL	
50	A5	I	SSTL	
157	A6	I	SSTL	
48	A7	I	SSTL	
155	A8	I	SSTL	
154	A9	I	SSTL	
54	A10	I	SSTL	
	AP	I	SSTL	
47	A11	I	SSTL	
153	A12	I	SSTL	
167	A13	I	SSTL	<b>Address Input 13</b> <i>Note: modules based on <math>\times 4/\times 8</math> component</i>
	NC	NC	–	<i>Note: modules based on <math>\times 16</math> component</i>

**Table 5 Pin Configuration of MDIMM (cont'd)**

Pin#	Name	Pin Type	Buffer Type	Function
<b>Data Signals</b>				
3	DQ0	I/O	SSTL	<b>Data Bus 63:0</b> Note: Data Input/Output pins
4	DQ1	I/O	SSTL	
9	DQ2	I/O	SSTL	
10	DQ3	I/O	SSTL	
109	DQ4	I/O	SSTL	
110	DQ5	I/O	SSTL	
114	DQ6	I/O	SSTL	
115	DQ7	I/O	SSTL	
12	DQ8	I/O	SSTL	
13	DQ9	I/O	SSTL	
21	DQ10	I/O	SSTL	
22	DQ11	I/O	SSTL	
117	DQ12	I/O	SSTL	
118	DQ13	I/O	SSTL	
125	DQ14	I/O	SSTL	
126	DQ15	I/O	SSTL	
24	DQ16	I/O	SSTL	
25	DQ17	I/O	SSTL	
30	DQ18	I/O	SSTL	
31	DQ19	I/O	SSTL	
128	DQ20	I/O	SSTL	
129	DQ21	I/O	SSTL	

**Table 5 Pin Configuration of MDIMM (cont'd)**

Pin#	Name	Pin Type	Buffer Type	Function
133	DQ22	I/O	SSTL	<b>Data Bus 63:0</b>
134	DQ23	I/O	SSTL	
33	DQ24	I/O	SSTL	
34	DQ25	I/O	SSTL	
38	DQ26	I/O	SSTL	
39	DQ27	I/O	SSTL	
136	DQ28	I/O	SSTL	
137	DQ29	I/O	SSTL	
142	DQ30	I/O	SSTL	
143	DQ31	I/O	SSTL	
67	DQ32	I/O	SSTL	
68	DQ33	I/O	SSTL	
73	DQ34	I/O	SSTL	
74	DQ35	I/O	SSTL	
174	DQ36	I/O	SSTL	
175	DQ37	I/O	SSTL	
179	DQ38	I/O	SSTL	
180	DQ39	I/O	SSTL	
76	DQ40	I/O	SSTL	
77	DQ41	I/O	SSTL	
81	DQ42	I/O	SSTL	
82	DQ43	I/O	SSTL	
182	DQ44	I/O	SSTL	
183	DQ45	I/O	SSTL	
188	DQ46	I/O	SSTL	
189	DQ47	I/O	SSTL	
84	DQ48	I/O	SSTL	
85	DQ49	I/O	SSTL	
92	DQ50	I/O	SSTL	
93	DQ51	I/O	SSTL	
191	DQ52	I/O	SSTL	
192	DQ53	I/O	SSTL	
200	DQ54	I/O	SSTL	
201	DQ55	I/O	SSTL	
95	DQ56	I/O	SSTL	
96	DQ57	I/O	SSTL	
101	DQ58	I/O	SSTL	
102	DQ59	I/O	SSTL	
203	DQ60	I/O	SSTL	
204	DQ61	I/O	SSTL	

**Table 5 Pin Configuration of MDIMM (cont'd)**

Pin#	Name	Pin Type	Buffer Type	Function
208	DQ62	I/O	SSTL	<b>Data Bus 63:0</b>
209	DQ63	I/O	SSTL	
7	DQS0	I/O	SSTL	<b>Data Strobes 7:0</b>  <i>Note: The data strobes, associated with one data byte, sourced with data transfers. In Write mode, the data strobe is sourced by the controller and is centered in the data window. In Read mode the data strobe is sourced by the DDR2 SDRAM and is sent at the leading edge of the data window. DQS signals are complements, and timing is relative to the crosspoint of respective DQS and <math>\overline{DQS}</math>. If the module is to be operated in single ended strobe mode, all DQS signals must be tied on the system board to <math>V_{SS}</math> and DDR2 SDRAM mode registers programmed appropriately.</i>
6	$\overline{DQS0}$	I/O	SSTL	
19	DQS1	I/O	SSTL	
18	$\overline{DQS1}$	I/O	SSTL	
28	DQS2	I/O	SSTL	
27	$\overline{DQS2}$	I/O	SSTL	
140	DQS3	I/O	SSTL	
139	$\overline{DQS3}$	I/O	SSTL	
71	DQS4	I/O	SSTL	
70	$\overline{DQS4}$	I/O	SSTL	
186	DQS5	I/O	SSTL	
185	$\overline{DQS5}$	I/O	SSTL	
198	DQS6	I/O	SSTL	
197	$\overline{DQS6}$	I/O	SSTL	
99	DQS7	I/O	SSTL	
98	$\overline{DQS7}$	I/O	SSTL	
112	DM0	I	SSTL	<b>Data Masks 7:0</b>  <i>Note: The data write masks, associated with one data byte. In Write mode, DM operates as a byte mask by allowing input data to be written if it is LOW but blocks the write operation if it is HIGH. In Read mode, DM lines have no effect.</i>  <i>Note: <math>\times 8</math> based module</i>
120	DM1	I	SSTL	
131	DM2	I	SSTL	
36	DM3	I	SSTL	
177	DM4	I	SSTL	
79	DM5	I	SSTL	
90	DM6	I	SSTL	
206	DM7	I	SSTL	
<b>EEPROM</b>				
105	SCL	I	CMOS	<b>Serial Bus Clock</b> <i>Note: This signal is used to clock data into and out of the SPD EEPROM.</i>
104	SDA	I/O	OD	<b>Serial Bus Data</b> <i>Note: This is a bidirectional pin used to transfer data into or out of the SPD EEPROM. A resistor must be connected from SDA to <math>V_{DDSPD}</math> on the motherboard to act as a pull-up.</i>
211	SA0	I	CMOS	<b>Serial Address Select Bus 1:0</b> <i>Note: Address pins used to select the Serial Presence Detect base address.</i>
213	SA1	I	CMOS	
<b>Power Supplies</b>				
1	$V_{REF}$	AI	–	<b>I/O Reference Voltage</b> <i>Note: Reference voltage for the SSTL-18 inputs.</i>

**Table 5 Pin Configuration of MDIMM (cont'd)**

Pin#	Name	Pin Type	Buffer Type	Function
42, 45, 49, 53, 57, 61, 64, 146, 149, 152, 156, 160, 164, 168, 171	V <sub>DD</sub>	PWR	–	<b>Power Supply</b> <i>Note: Power and ground for the DDR SDRAM</i>
107	V <sub>DDSPD</sub>	PWR	–	<b>EEPROM Power Supply</b> <i>Note: Serial EEPROM positive power supply, wired to a separate power pin at the connector which supports from 1.7 Volt to 3.6 Volt.</i>
2, 5, 8, 11, 14, 17, 20, 23, 26, 29, 32, 35, 37, 40, 66, 69, 72, 75, 78, 80, 83, 86, 89, 91, 94, 97, 100, 103, 108, 111, 113, 116, 119, 121, 124, 127, 130, 132, 135, 138, 141, 144, 173, 176, 178, 181, 184, 187, 190, 193, 196, 205, 199, 202, 207, 210	V <sub>SS</sub>	GND	–	<b>Ground Plane</b> <i>Note: Power and ground for the DDR SDRAM</i>
<b>Other Pins</b>				
166	ODT0	I	SSTL	<b>On-Die Termination Control 1:0</b>
63	ODT1	I	SSTL	<i>Note: Asserts on-die termination for DQ, DM, DQS, and DQS signals if enabled via the DDR2 SDRAM mode register.</i> <i>Note: 2-rank module</i>
	NC			<i>Note: 1-rank module</i>
15, 16, 41, 44, 58, 59, 65, 87, 88, 106, 145, 148, 150, 151, 167, 169, 170, 172, 212, 214	NC	NC	–	<b>Not connected</b> <i>Note: Pins not connected on Infineon MDIMMs</i>

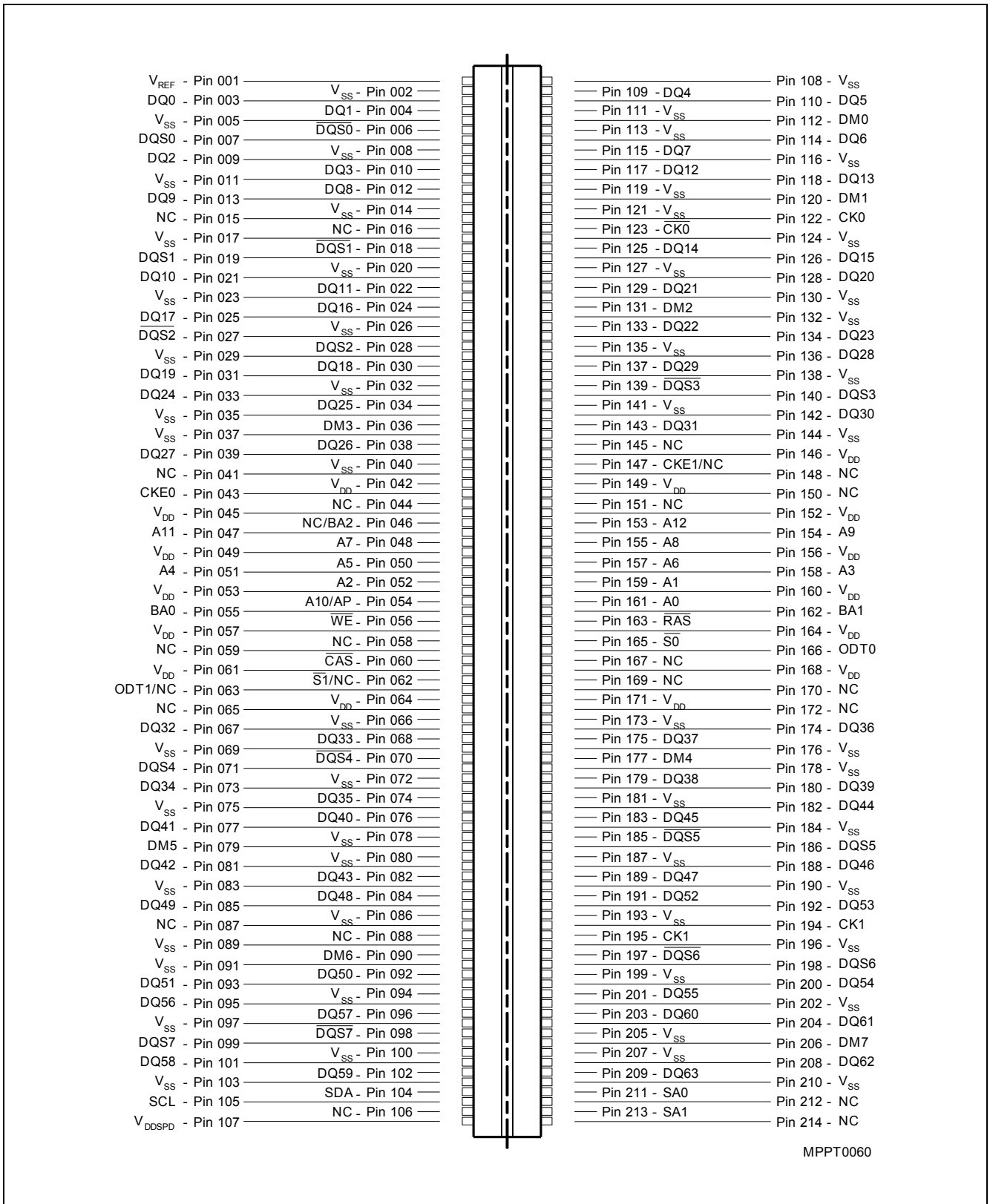
**Table 6 Abbreviations for Pin Type**

Abbreviation	Description
I	Standard input-only pin. Digital levels.
O	Output. Digital levels.
I/O	I/O is a bidirectional input/output signal.
AI	Input. Analog levels.
PWR	Power
GND	Ground
NC	Not Connected

**Table 7 Abbreviations for Buffer Type**

Abbreviation	Description
SSTL	Serial Stub Terminated Logic (SSTL_18)
CMOS	CMOS Levels
OD	Open Drain. The corresponding pin has 2 operational states, active low and tristate, and allows multiple devices to share as a wire-OR.

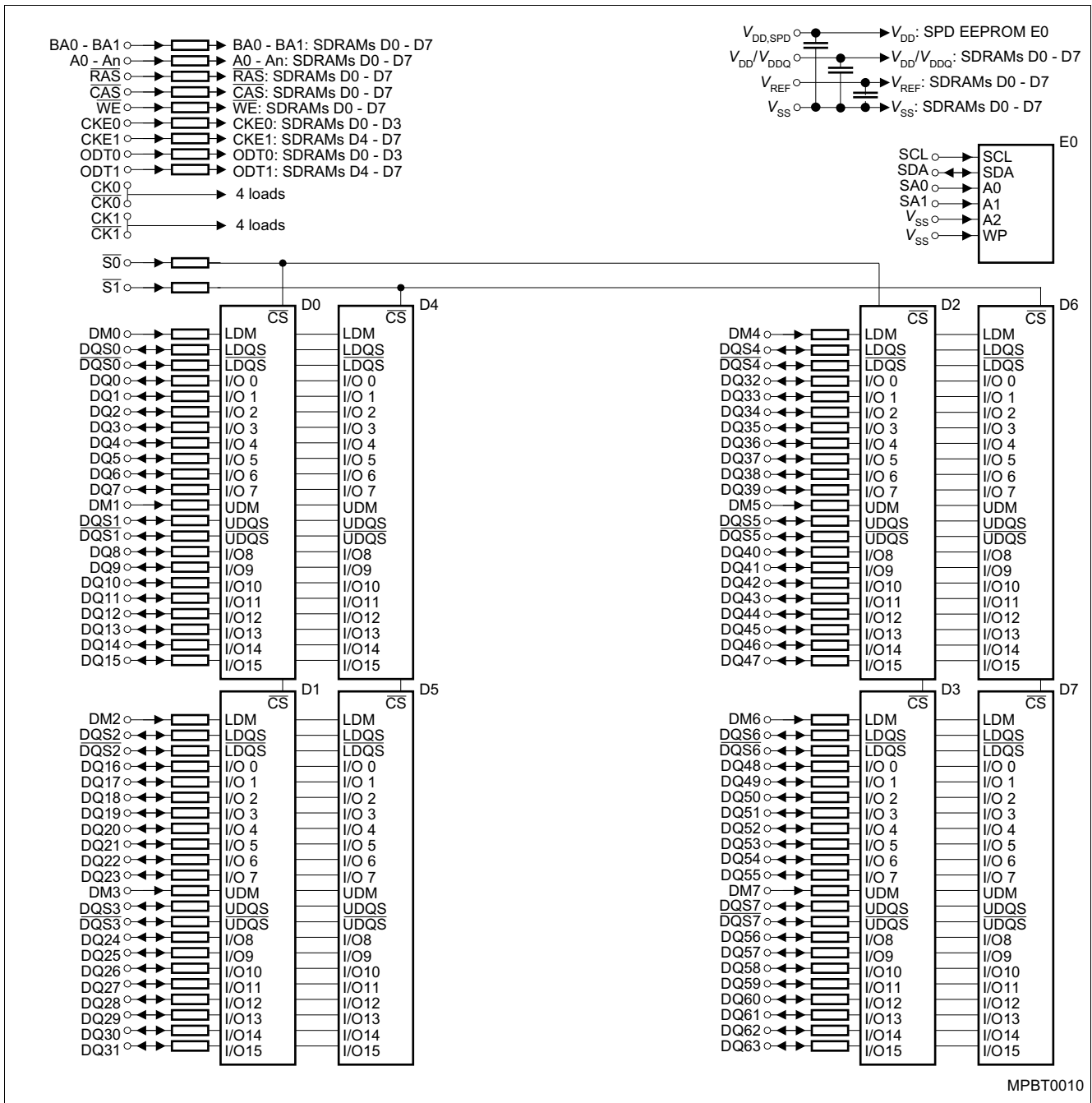
**Pin Configuration**



MPPT0060

**Figure 1 Pin Configuration for Two-Piece Mezzanine Socket on MDIMM (214 pins)**

**2.1 Block Diagrams**



**Figure 2 Block Diagram Raw Card A Micro DIMM (x64, 2 Ranks, x16)**

**Notes**

1. DQ, DQS, DM resistors are  $22 \Omega \pm 5 \%$
2.  $\overline{S0}$ ,  $\overline{S1}$ ,  $\overline{BA_n}$ ,  $\overline{A_n}$ ,  $\overline{RAS}$ ,  $\overline{CAS}$ ,  $\overline{WE}$ ,  $\overline{ODT0}$ ,  $\overline{ODT1}$ ,  $\overline{CKE0}$ ,  $\overline{CKE1}$  resistors are  $3 \Omega \pm 5 \%$



### 3 $I_{DD}$ Specifications and Conditions

**Table 8**  $I_{DD}$  Measurement Conditions<sup>1)2)3)4)5)6)</sup>

Parameter	Symbol
<b>Operating Current 0</b> One bank Active - Precharge; $t_{CK} = t_{CK.MIN}$ , $t_{RC} = t_{RC.MIN}$ , $t_{RAS} = t_{RAS.MIN}$ , CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are SWITCHING, Databus inputs are SWITCHING.	$I_{DD0}$
<b>Operating Current 1</b> One bank Active - Read - Precharge; $I_{OUT} = 0$ mA, BL = 4, $t_{CK} = t_{CK.MIN}$ , $t_{RC} = t_{RC.MIN}$ , $t_{RAS} = t_{RAS.MIN}$ , $t_{RCD} = t_{RCD.MIN}$ , AL = 0, CL = CL <sub>MIN</sub> ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are SWITCHING, Databus inputs are SWITCHING.	$I_{DD1}$
<b>Precharge Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; CKE is HIGH; $t_{CK} = t_{CK.MIN}$ ; Other control and address inputs are SWITCHING, Data bus inputs are SWITCHING.	$I_{DD2N}$
<b>Precharge Power-Down Current</b> Other control and address inputs are STABLE, Data bus inputs are FLOATING.	$I_{DD2P}$
<b>Precharge Quiet Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; CKE is HIGH; $t_{CK} = t_{CK.MIN}$ ; Other control and address inputs are STABLE, Data bus inputs are FLOATING.	$I_{DD2Q}$
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK.MIN}$ , CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are FLOATING. MRS A12 bit is set to LOW (Fast Power-down Exit);	$I_{DD3P(0)}$
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK.MIN}$ , CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are FLOATING. MRS A12 bit is set to HIGH (Slow Power-down Exit);	$I_{DD3P(1)}$
<b>Active Standby Current</b> Burst Read: All banks open; Continuous burst reads; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CK.MIN}$ ; $t_{RAS} = t_{RAS.MAX}$ , $t_{RP} = t_{RP.MIN}$ ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are SWITCHING; Data Bus inputs are SWITCHING; $I_{OUT} = 0$ mA.	$I_{DD3N}$
<b>Operating Current</b> Burst Read: All banks open; Continuous burst reads; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CK.MIN}$ ; $t_{RAS} = t_{RAS.MAX}$ , $t_{RP} = t_{RP.MIN}$ ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are SWITCHING; Data Bus inputs are SWITCHING; $I_{OUT} = 0$ mA.	$I_{DD4R}$
<b>Operating Current</b> Burst Write: All banks open; Continuous burst writes; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CK.MIN}$ ; $t_{RAS} = t_{RAS.MAX}$ , $t_{RP} = t_{RP.MAX}$ ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are SWITCHING; Data Bus inputs are SWITCHING;	$I_{DD4W}$
<b>Burst Refresh Current</b> $t_{CK} = t_{CK.MIN}$ , Refresh command every $t_{RFC} = t_{RFC.MIN}$ interval, CKE is HIGH, $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are SWITCHING, Data bus inputs are SWITCHING.	$I_{DD5B}$
<b>Distributed Refresh Current</b> $t_{CK} = t_{CK.MIN}$ , Refresh command every $t_{RFC} = t_{REFI}$ interval, CKE is LOW and $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are SWITCHING, Data bus inputs are SWITCHING.	$I_{DD5D}$

**I<sub>DD</sub> Specifications and Conditions**

**Table 8 I<sub>DD</sub> Measurement Conditions<sup>1)2)3)4)5)6)</sup>**

Parameter	Symbol
<b>Self-Refresh Current</b> CKE ≤ 0.2 V; external clock off, CK and $\overline{CK}$ at 0 V; Other control and address inputs are FLOATING, Data bus inputs are FLOATING. I <sub>DD6</sub> current values are guaranteed up to T <sub>CASE</sub> of 85 °C max.	I <sub>DD6</sub>
<b>All Bank Interleave Read Current</b> All banks are being interleaved at minimum t <sub>RC</sub> without violating t <sub>RRD</sub> using a burst length of 4. Control and address bus inputs are STABLE during DESELECTS. I <sub>out</sub> = 0 mA.	I <sub>DD7</sub>

- 1) V<sub>DDQ</sub> = 1.8 V ± 0.1 V; V<sub>DD</sub> = 1.8 V ± 0.1 V
- 2) I<sub>DD</sub> specifications are tested after the device is properly initialized and I<sub>DD</sub> parameter are specified with ODT disabled.
- 3) Definitions for I<sub>DD</sub>:  
 LOW is defined as V<sub>IN</sub> ≤ V<sub>IL(ac).MAX</sub>, HIGH is defined as V<sub>IN</sub> ≥ V<sub>IH(ac).MIN</sub>  
 STABLE is defined as: inputs are stable at a HIGH or LOW level  
 FLOATING is defined as: inputs are V<sub>REF</sub> = V<sub>DDQ</sub> / 2  
 SWITCHING is defined as: inputs are changing between HIGH and LOW every other clock (once per 2 cycles) for address and control signals, and inputs changing between HIGH and LOW every other data transfer (once per cycle) for DQ signals not including mask or strobes.
- 4) I<sub>DD1</sub>, I<sub>DD4R</sub> and I<sub>DD7</sub> current measurements are defined with the outputs disabled (I<sub>OUT</sub> = 0 mA). To achieve this on module level the output buffers can be disabled using an EMRS(1) (Extended Mode Register Command) by setting A12 bit to HIGH.
- 5) For two rank modules: for all active current measurements the other rank is in Precharge Power-Down Mode I<sub>DD2P</sub>
- 6) For details and notes see the relevant INFINEON component data sheet

**Table 9**  $I_{DD}$  Specification for HYS64T128020HM-[-3.7/-5]-A

Product Type	HYS64T128020HM-3.7-A	HYS64T128020HM-5-A	Unit	Notes
<b>Organization</b>	<b>1 GB</b>	<b>1 GB</b>		
	<b>2 Ranks</b>	<b>2 Ranks</b>		
	<b>×64</b>	<b>×64</b>		
	<b>-3.7</b>	<b>-5</b>		
<b>Symbol</b>	<b>Max.</b>	<b>Max.</b>		
$I_{DD0}$	340	320	mA	1)
$I_{DD1}$	400	380	mA	1)
$I_{DD2P}$	40	40	mA	1)
$I_{DD2N}$	370	280	mA	1)
$I_{DD2Q}$	260	220	mA	1)
$I_{DD3P(MRS = 0)}$	140	100	mA	1)
$I_{DD3P(MRS = 1)}$	50	40	mA	1)
$I_{DD3N}$	400	320	mA	1)
$I_{DD4R}$	540	440	mA	1)
$I_{DD4W}$	680	540	mA	1)
$I_{DD5B}$	760	740	mA	1)
$I_{DD5D}$	60	60	mA	1)
$I_{DD6(L)}$	32	32	mA	1)
$I_{DD7}$	1100	1040	mA	1)

1) Calculated values from component data. ODT disabled.  $I_{DD1}$ ,  $I_{DD4R}$ , and  $I_{DD7}$  are defined with the outputs disabled.

### 3.1 $I_{DD}$ Test Conditions

For testing the  $I_{DD}$  parameters, the timing parameters as in [Table 10](#) are used.

**Table 10**  $I_{DD}$  Measurement Test Conditions

Parameter	Symbol	-3.7	-5	Unit
		PC2-4200-4-4-4	PC2-3200-3-3-3	
CAS Latency	$CL_{(IDD)}$	4	3	$t_{CK}$
Clock Cycle Time	$t_{CK(IDD)}$	3.75	5	ns
Active to Read or Write delay	$t_{RCD(IDD)}$	15	15	ns
Active to Active / Auto-Refresh command period	$t_{RC(IDD)}$	60	55	ns
Active bank A to Active bank B command delay	$t_{RRD(IDD)}$	10	10	ns
Active to Precharge Command	$t_{RAS.MIN(IDD)}$	45	40	ns
	$t_{RAS.MAX(IDD)}$	70000	70000	ns
Precharge Command Period	$t_{RP(IDD)}$	15	15	ns
Auto-Refresh to Active / Auto-Refresh command period	$t_{RFC(IDD)}$	127.5	127.5	ns
Average periodic Refresh interval	$t_{REFI}$	7.8	7.8	$\mu$ s

### 3.2 On Die Termination (ODT) Current

The ODT function adds additional current consumption to the DDR2 SDRAM when enabled by the EMRS(1). Depending on address bits A[6,2] in the EMRS(1) a “weak” or “strong” termination can be selected. The

current consumption for any terminated input pin, depends on the input pin is in tri-state or driving 0 or 1, as long as ODT is enabled during a given period of time.

**Table 11** ODT current per terminated pin

Parameter	Symbol	Min.	Typ.	Max.	Unit	EMRS(1) State
<b>Enabled ODT current per DQ</b> ODT is HIGH; Data Bus inputs are FLOATING	$I_{ODTO}$	5	6	7.5	mA/DQ	A6 = 0, A2 = 1
		2.5	3	3.75	mA/DQ	A6 = 1, A2 = 0
<b>Active ODT current per DQ</b> ODT is HIGH; worst case of Data Bus inputs are STABLE or SWITCHING.	$I_{ODTT}$	10	12	15	mA/DQ	A6 = 0, A2 = 1
		5	6	7.5	mA/DQ	A6 = 1, A2 = 0

*Note: For power consumption calculations the ODT duty cycle has to be taken into account*

## 4 Electrical Characteristics

### 4.1 Operating Conditions

**Table 12 Absolute Maximum Ratings**

Parameter	Symbol	Values		Unit	Note/Test Condition
		Min.	Max.		
Voltage on any pins relative to $V_{SS}$	$V_{IN}, V_{OUT}$	- 0.5	2.3	V	1)
Voltage on $V_{DD}$ relative to $V_{SS}$	$V_{DD}$	- 1.0	2.3	V	1)
Voltage on $V_{DDQ}$ relative to $V_{SS}$	$V_{DDQ}$	- 0.5	2.3	V	1)
Storage Humidity (without condensation)	$H_{STG}$	5	95	%	1)

- 1) Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and device functional operation at or above the conditions indicated is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability

**Table 13 Operating Conditions**

Parameter	Symbol	Values		Unit	Notes
		Min.	Max.		
Operating temperature (ambient)	$T_{OPR}$	0	+65	°C	
DRAM Case Temperature	$T_{CASE}$	0	+95	°C	1)2)3)4)
Storage Temperature	$T_{STG}$	-50	+100	°C	
Barometric Pressure (operating & storage)	$P_{BAR}$	+69	+105	kPa	5)
Operating Humidity (relative)	$H_{OPR}$	10	90	%	

- 1) DRAM Component Case Temperature is the surface temperature in the center on the top side of any of the DRAMs.
- 2) Within the DRAM Component Case Temperature Range all DRAM specifications will be supported
- 3) Above 85 °C DRAM Case Temperature the Auto-Refresh command interval has to be reduced to  $t_{REFI} = 3.9 \mu s$
- 4) Self-Refresh period is hard-coded in the DRAMs and therefore it is imperative that the system ensures the DRAM is below 85 °C Case Temperature before initiating Self-Refresh operation.
- 5) Up to 3000 m.

**Table 14 Supply Voltage Levels and DC Operating Conditions**

Parameter	Symbol	Values			Unit	Notes
		Min.	Nom.	Max.		
Device Supply Voltage	$V_{DD}$	1.7	1.8	1.9	V	—
Output Supply Voltage	$V_{DDQ}$	1.7	1.8	1.9	V	1)
Input Reference Voltage	$V_{REF}$	$0.49 \times V_{DDQ}$	$0.5 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	V	2)
SPD Supply Voltage	$V_{DDSPD}$	1.7	—	3.6	V	
DC Input Logic High	$V_{IH(DC)}$	$V_{REF} + 0.125$	—	$V_{DDQ} + 0.3$	V	
DC Input Logic Low	$V_{IL(DC)}$	- 0.30	—	$V_{REF} - 0.125$	V	
In / Output Leakage Current	$I_L$	- 5	—	5	$\mu A$	3)

- 1) Under all conditions,  $V_{DDQ}$  must be less than or equal to  $V_{DD}$
- 2) Peak to peak AC noise on  $V_{REF}$  may not exceed  $\pm 2\% V_{REF(DC)}$ .  $V_{REF}$  is also expected to track noise in  $V_{DDQ}$ .
- 3) Input voltage for any connector pin under test of  $0 V \leq V_{IN} \leq V_{DDQ} + 0.3 V$ ; all other pins at 0 V. Current is per pin

Table 15 Speed Grade Definition Speed Bins

Speed Grade		DDR2-533C		DDR2-400B		Unit	Notes	
IFX Sort Name		-3.7		-5				
CAS-RCD-RP latencies		4-4-4		3-3-3		$t_{CK}$		
Parameter	Symbol	Min.	Max.	Min.	Max.	—		
Clock Frequency	@ CL = 3	$t_{CK}$	5	8	5	8	ns	1)2)3)4)
	@ CL = 4	$t_{CK}$	3.75	8	5	8	ns	1)2)3)4)
	@ CL = 5	$t_{CK}$	3.75	8	5	8	ns	1)2)3)4)
Row Active Time	$t_{RAS}$	45	70000	40	70000	ns	1)2)3)4)5)	
Row Cycle Time	$t_{RC}$	60	—	55	—	ns	1)2)3)4)	
RAS-CAS-Delay	$t_{RCD}$	15	—	15	—	ns	1)2)3)4)	
Row Precharge Time	$t_{RP}$	15	—	15	—	ns	1)2)3)4)	

- 1) Timings are guaranteed with  $CK/\overline{CK}$  differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode. Timings are further guaranteed for normal OCD drive strength (EMRS(1) A1 = 0) only.
- 2) The  $CK/\overline{CK}$  input reference level (for timing reference to  $CK/\overline{CK}$ ) is the point at which CK and  $\overline{CK}$  cross. The  $DQS / \overline{DQS}$ ,  $RDQS / \overline{RDQS}$ , input reference level is the crosspoint when in differential strobe mode
- 3) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes,  $CKE = 0.2 \times V_{DDQ}$  is recognized as low.
- 4) The output timing reference voltage level is  $V_{TT}$ .
- 5)  $t_{RAS,MAX}$  is calculated from the maximum amount of time a DDR2 device can operate without a refresh command which is equal to  $9 \times t_{REFI}$ .

Table 16 Timing Parameter by Speed Grade - DDR2-400B & DDR2-533C

Parameter	Symbol	-3.7 DDR2-533 4-4-4		-5 DDR2-400 3-3-3		Unit	Notes <sup>1)</sup>
		Min.	Max.	Min.	Max.		
DQ output access time from $CK / \overline{CK}$	$t_{AC}$	-500	+500	-600	+600	ps	
$\overline{CAS}$ A to $\overline{CAS}$ B command period	$t_{CCD}$	2	—	2	—	$t_{CK}$	
CK, $\overline{CK}$ high-level width	$t_{CH}$	0.45	0.55	0.45	0.55	$t_{CK}$	
CKE minimum high and low pulse width	$t_{CKE}$	3	—	3	—	$t_{CK}$	
CK, $\overline{CK}$ low-level width	$t_{CL}$	0.45	0.55	0.45	0.55	$t_{CK}$	
Auto-Precharge write recovery + precharge time	$t_{DAL}$	WR + $t_{RP}$	—	WR + $t_{RP}$	—	$t_{CK}$	
Minimum time clocks remain ON after CKE asynchronously drops LOW	$t_{DELAY}$	$t_{IS} + t_{CK} + t_{IH}$	—	$t_{IS} + t_{CK} + t_{IH}$	—	ns	
DQ and DM input hold time (differential data strobe)	$t_{DH}(\text{base})$	225	—	275	—	ps	
DQ and DM input hold time (single ended data strobe)	$t_{DH1}(\text{base})$	-25	—	25	—	ps	
DQ and DM input pulse width (each input)	$t_{DIPW}$	0.35	—	0.35	—	$t_{CK}$	
DQS output access time from $CK / \overline{CK}$	$t_{DQSCK}$	-450	+450	-500	+500	ps	

**Electrical Characteristics**
**Table 16 Timing Parameter by Speed Grade - DDR2-400B & DDR2-533C**

Parameter	Symbol	-3.7 DDR2-533 4-4-4		-5 DDR2-400 3-3-3		Unit	Notes <sup>1)</sup>
		Min.	Max.	Min.	Max.		
		DQS input low (high) pulse width (write cycle)	$t_{DQSL,H}$	0.35	—		
DQS-DQ skew (for DQS & associated DQ signals)	$t_{DQSQ}$	—	300	—	350	ps	
Write command to 1st DQS latching transition	$t_{DQSS}$	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	$t_{CK}$	
DQ and DM input setup time (differential data strobe)	$t_{DS}(\text{base})$	100	—	150	—	ps	
DQ and DM input setup time (single ended data strobe)	$t_{DS1}(\text{base})$	-25	—	25	—	ps	
DQS falling edge hold time from CK (write cycle)	$t_{DSH}$	0.2	—	0.2	—	$t_{CK}$	
DQS falling edge to CK setup time (write cycle)	$t_{DSS}$	0.2	—	0.2	—	$t_{CK}$	
Four Activate Window period	$t_{FAW}$	37.5	—	37.5	—	ns	2)3)
		50	—	50	—	ns	4)
Clock half period	$t_{HP}$	MIN. ( $t_{CL}, t_{CH}$ )		MIN. ( $t_{CL}, t_{CH}$ )			
Data-out high-impedance time from CK / $\overline{CK}$	$t_{HZ}$	—	$t_{AC,MAX}$	—	$t_{AC,MAX}$	ps	
Address and control input hold time	$t_{IH}(\text{base})$	375	—	475	—	ps	
Address and control input pulse width (each input)	$t_{IPW}$	0.6	—	0.6	—	$t_{CK}$	
Address and control input setup time	$t_{IS}(\text{base})$	250	—	350	—	ps	
DQ low-impedance time from CK / $\overline{CK}$	$t_{LZ(DQ)}$	$2 \times t_{AC,MIN}$	$t_{AC,MAX}$	$2 \times t_{AC,MIN}$	$t_{AC,MAX}$	ps	
DQS low-impedance from CK / $\overline{CK}$	$t_{LZ(DQS)}$	$t_{AC,MIN}$	$t_{AC,MAX}$	$t_{AC,MIN}$	$t_{AC,MAX}$	ps	
Mode register set command cycle time	$t_{MRD}$	2	—	2	—	$t_{CK}$	
OCD drive mode output delay	$t_{OIT}$	0	12	0	12	ns	
Data output hold time from DQS	$t_{QH}$	$t_{HP} - t_{QHS}$	—	$t_{HPQ} - t_{QHS}$	—		
Data hold skew factor	$t_{QHS}$	—	400	—	450	ps	
Average periodic refresh Interval	$t_{REFI}$	—	7.8	—	7.8	$\mu\text{s}$	5)
		—	3.9	—	3.9	$\mu\text{s}$	6)
Auto-Refresh to Active/Auto-Refresh command period	$t_{RFC}$	127.5	—	127.5	—	ns	
Precharge-All (8 banks) command period	$t_{RP}$	$15 + 1t_{CK}$	—	$15 + 1t_{CK}$	—	ns	
Read preamble	$t_{RPRE}$	0.9	1.1	0.9	1.1	$t_{CK}$	
Read postamble	$t_{RPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	

Table 16 Timing Parameter by Speed Grade - DDR2-400B & DDR2-533C

Parameter	Symbol	-3.7 DDR2-533 4-4-4		-5 DDR2-400 3-3-3		Unit	Notes <sup>1)</sup>
		Min.	Max.	Min.	Max.		
		Active bank A to Active bank B command period	$t_{RRD}$	7.5 10	—		
Internal Read to Precharge command delay	$t_{RTP}$	7.5	—	7.5	—	ns	
Write preamble	$t_{WPRE}$	$0.35 \times t_{CK}$	—	$0.35 \times t_{CK}$	—	$t_{CK}$	
Write postamble	$t_{WPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	
Write recovery time for write without Auto-Precharge	$t_{WR}$	15	—	15	—	ns	
Write recovery time for write with Auto-Precharge	WR	$t_{WR}/t_{CK}$		$t_{WR}/t_{CK}$		$t_{CK}$	
Internal Write to Read command delay	$t_{WTR}$	7.5	—	10	—	ns	
Exit power down to any valid command (other than NOP or Deselect)	$t_{XARD}$	2	—	2	—	$t_{CK}$	
Exit active power-down mode to Read command (slow exit, lower power)	$t_{XARDS}$	6 – AL	—	6 – AL	—	$t_{CK}$	
Exit precharge power-down to any valid command (other than NOP or Deselect)	$t_{XP}$	2	—	2	—	$t_{CK}$	
Exit Self-Refresh to non-Read command	$t_{XSNR}$	$t_{RFC} + 10$	—	$t_{RFC} + 10$	—	ns	
Exit Self-Refresh to Read command	$t_{XSRD}$	200	—	200	—	$t_{CK}$	

- 1) For details and notes see the relevant INFINEON component data sheet
- 2)  $\times 4$  &  $\times 8$  (1k page size)
- 3) 8 bank device Sequential Activation Restriction. No more than 4 banks may be activated in a rolling  $t_{FAW}$  window.
- 4)  $\times 16$  (2k page size), not on 256 Mbit component
- 5)  $0 \leq T_{CASE} \leq 85 \text{ }^\circ\text{C}$
- 6)  $85 \text{ }^\circ\text{C} < T_{CASE} \leq 95 \text{ }^\circ\text{C}$



**Table 17 ODT AC Electrical Characteristics and Operating Conditions**

Symbol	Parameter / Condition	Values		Unit	Notes
		Min.	Max.		
$t_{AOND}$	ODT turn-on delay	2	2	$t_{CK}$	
$t_{AON}$	ODT turn-on	$t_{AC.MIN}$	$t_{AC.MAX} + 1 \text{ ns}$	ns	1)
$t_{AONPD}$	ODT turn-on (Power-Down Modes)	$t_{AC.MIN} + 2 \text{ ns}$	$2 t_{CK} + t_{AC.MAX} + 1 \text{ ns}$	ns	
$t_{AOFD}$	ODT turn-off delay	2.5	2.5	$t_{CK}$	
$t_{AOF}$	ODT turn-off	$t_{AC.MIN}$	$t_{AC.MAX} + 0.6 \text{ ns}$	ns	2)
$t_{AOFPD}$	ODT turn-off (Power-Down Modes)	$t_{AC.MIN} + 2 \text{ ns}$	$2.5 t_{CK} + t_{AC.MAX} + 1 \text{ ns}$	ns	
$t_{ANPD}$	ODT to Power Down Mode Entry Latency	3	—	$t_{CK}$	
$t_{AXPD}$	ODT Power Down Exit Latency	8	—	$t_{CK}$	

1) ODT turn on time min. is when the device leaves high impedance and ODT resistance begins to turn on. ODT turn on time max is when the ODT resistance is fully on. Both are measure from  $t_{AOND}$ .

2) ODT turn off time min. is when the device starts to turn off ODT resistance. ODT turn off time max is when the bus is in high impedance. Both are measured from  $t_{AOFD}$ .

## 5 SPD Codes

Table 18 SPD Codes for HYS64T128020HM-[3.7/5]-A

Product Type		HYS64T128020HM-3.7-A	HYS64T128020HM-5-A
<b>Organization</b>		<b>1 GByte</b>	<b>1 GByte</b>
		<b>×64</b>	<b>×64</b>
		<b>2 Ranks (×16)</b>	<b>2 Ranks (×16)</b>
<b>Label Code</b>		<b>PC2-4200M-444</b>	<b>PC2-3200M-333</b>
<b>JEDEC SPD Revision</b>		<b>Rev. 1.1</b>	<b>Rev. 1.1</b>
Byte#	Description	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80
1	Total number of Bytes in EEPROM	08	08
2	Memory Type (DDR2)	08	08
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	DIMM Rank and Stacking Information	61	61
6	Data Width	40	40
7	Not used	00	00
8	Interface Voltage Level	05	05
9	$t_{CK} @ CL_{max}$ (Byte 18) [ns]	3D	50
10	$t_{AC}$ SDRAM @ $CL_{max}$ (Byte 18) [ns]	50	60
11	Error Correction Support (non-ECC, ECC)	00	00
12	Refresh Rate and Type	82	82
13	Primary SDRAM Width	10	10
14	Error Checking SDRAM Width	00	00
15	Not used	00	00
16	Burst Length Supported	0C	0C
17	Number of Banks on SDRAM Device	08	08
18	Supported CAS Latencies	38	38
19	DIMM Mechanical Characteristics	00	00
20	DIMM Type Information	08	08
21	DIMM Attributes	00	00
22	Component Attributes	01	01
23	$t_{CK} @ CL_{max} -1$ (Byte 18) [ns]	3D	50
24	$t_{AC}$ SDRAM @ $CL_{max} -1$ [ns]	50	60
25	$t_{CK} @ CL_{max} -2$ (Byte 18) [ns]	50	50

Table 18 SPD Codes for HYS64T128020HM-[3.7/5]-A

Product Type		HYS64T128020HM-3.7-A	HYS64T128020HM-5-A
<b>Organization</b>		<b>1 GByte</b>	<b>1 GByte</b>
		<b>×64</b>	<b>×64</b>
		<b>2 Ranks (×16)</b>	<b>2 Ranks (×16)</b>
<b>Label Code</b>		<b>PC2-4200M-444</b>	<b>PC2-3200M-333</b>
<b>JEDEC SPD Revision</b>		<b>Rev. 1.1</b>	<b>Rev. 1.1</b>
<b>Byte#</b>	<b>Description</b>	<b>HEX</b>	<b>HEX</b>
26	$t_{AC}$ SDRAM @ $CL_{max} -2$ [ns]	60	60
27	$t_{RP.MIN}$ [ns]	3C	3C
28	$t_{RRD.MIN}$ [ns]	28	28
29	$t_{RCD.MIN}$ [ns]	3C	3C
30	$t_{RAS.MIN}$ [ns]	2D	28
31	Module Density per Rank	80	80
32	$t_{AS.MIN}$ and $t_{CS.MIN}$ [ns]	25	35
33	$t_{AH.MIN}$ and $t_{CH.MIN}$ [ns]	37	47
34	$t_{DS.MIN}$ [ns]	10	15
35	$t_{DH.MIN}$ [ns]	22	27
36	$t_{WR.MIN}$ [ns]	3C	3C
37	$t_{WTR.MIN}$ [ns]	1E	28
38	$t_{RTP.MIN}$ [ns]	1E	1E
39	Analysis Characteristics	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00
41	$t_{RC.MIN}$ [ns]	3C	37
42	$t_{RFC.MIN}$ [ns]	7F	7F
43	$t_{CK.MAX}$ [ns]	80	80
44	$t_{DQSQ.MAX}$ [ns]	1E	23
45	$t_{QHS.MAX}$ [ns]	28	2D
46	PLL Relock Time	00	00
47	$T_{CASE.MAX}$ Delta / $\Delta T_{4R4W}$ Delta	57	55
48	Psi(T-A) DRAM	58	58
49	$\Delta T_0$ (DT0)	36	32
50	$\Delta T_{2N}$ (DT2N, UDIMM) or $\Delta T_{2Q}$ (DT2Q, RDIMM)	26	1D
51	$\Delta T_{2P}$ (DT2P)	1C	1C
52	$\Delta T_{3N}$ (DT3N)	1C	16
53	$\Delta T_{3P.FAST}$ (DT3P fast)	1C	16

Table 18 SPD Codes for HYS64T128020HM-[3.7/5]-A

Product Type		HYS64T128020HM-3.7-A	HYS64T128020HM-5-A
<b>Organization</b>		<b>1 GByte</b>	<b>1 GByte</b>
		<b>×64</b>	<b>×64</b>
		<b>2 Ranks (×16)</b>	<b>2 Ranks (×16)</b>
<b>Label Code</b>		<b>PC2-4200M-444</b>	<b>PC2-3200M-333</b>
<b>JEDEC SPD Revision</b>		<b>Rev. 1.1</b>	<b>Rev. 1.1</b>
<b>Byte#</b>	<b>Description</b>	<b>HEX</b>	<b>HEX</b>
54	$\Delta T_{3P,slow}$ (DT3P slow)	14	11
55	$\Delta T_{4R}$ (DT4R) / $\Delta T_{4R4W S}$ Sign (DT4R4W)	36	2C
56	$\Delta T_{5B}$ (DT5B)	1F	1E
57	$\Delta T_7$ (DT7)	2D	2B
58	Psi(ca) PLL	00	00
59	Psi(ca) REG	00	00
60	$\Delta T_{PLL}$ (DTPLL)	00	00
61	$\Delta T_{REG}$ (DTREG) / Toggle Rate	00	00
62	SPD Revision	11	11
63	Checksum of Bytes 0-62	D8	27
64	JEDEC ID Code of Infineon (1)	C1	C1
65 - 71	JEDEC ID Code of Infineon (2 - 8)	00	00
72	Module Manufacturer Location	xx	xx
73	Product Type, Char 1	36	36
74	Product Type, Char 2	34	34
75	Product Type, Char 3	54	54
76	Product Type, Char 4	31	31
77	Product Type, Char 5	32	32
78	Product Type, Char 6	38	38
79	Product Type, Char 7	30	30
80	Product Type, Char 8	32	32
81	Product Type, Char 9	30	30
82	Product Type, Char 10	48	48
83	Product Type, Char 11	4D	4D
84	Product Type, Char 12	33	35
85	Product Type, Char 13	2E	41
86	Product Type, Char 14	37	20
87	Product Type, Char 15	41	20

Table 18 SPD Codes for HYS64T128020HM-[3.7/5]-A

Product Type		HYS64T128020HM-3.7-A	HYS64T128020HM-5-A
<b>Organization</b>		<b>1 GByte</b> ×64 <b>2 Ranks (×16)</b>	<b>1 GByte</b> ×64 <b>2 Ranks (×16)</b>
<b>Label Code</b>		<b>PC2-4200M-444</b>	<b>PC2-3200M-333</b>
<b>JEDEC SPD Revision</b>		<b>Rev. 1.1</b>	<b>Rev. 1.1</b>
<b>Byte#</b>	<b>Description</b>	<b>HEX</b>	<b>HEX</b>
88	Product Type, Char 16	20	20
89	Product Type, Char 17	20	20
90	Product Type, Char 18	20	20
91	Module Revision Code	1x	1x
92	Test Program Revision Code	xx	xx
93	Module Manufacturing Date Year	xx	xx
94	Module Manufacturing Date Week	xx	xx
95	Module Serial Number (1)	xx	xx
96	Module Serial Number (2)	xx	xx
97	Module Serial Number (3)	xx	xx
98	Module Serial Number (4)	xx	xx
99 - 127	Not used	00	00



## 7 Product Type Nomenclature (DDR2 DRAMs and DIMMs)

Infineon's nomenclature uses simple coding combined with some proprietary coding. **Table 19** provides examples for module and component product type number as well as the field number. The detailed field description together with possible values and coding explanation is listed for modules in **Table 20** and for components in **Table 21**.

**Table 19 Nomenclature Fields and Examples**

Example for	Field Number										
	1	2	3	4	5	6	7	8	9	10	11
Micro-DIMM	HYS	64	T	128	0	2	0	K	M	-5	-A
DDR2 DRAM	HYB	18	T	1G	16		0	A	C	-5	

**Table 20 DDR2 DIMM Nomenclature**

Field	Description	Values	Coding
1	INFINEON Modul Prefix	HYS	Constant
2	Module Data Width [bit]	64	Non-ECC
		72	ECC
3	DRAM Technology	T	DDR2
4	Memory Density per I/O [Mbit]; Module Density <sup>1)</sup>	32	256 MByte
		64	512 MByte
		128	1 GByte
		256	2 GByte
5	Raw Card Generation	0 .. 9	look up table
6	Number of Module Ranks	0, 2, 4	1, 2, 4
7	Product Variations	0 .. 9	look up table
8	Package, Lead-Free Status	A .. Z	look up table
9	Module Type	D	SO-DIMM
		M	Micro-DIMM
		R	Registered
		U	Unbuffered
10	Speed Grade	-3.7	PC2-4200 4-4-4
		-5	PC2-3200 3-3-3
11	Die Revision	-A	First
		-B	Second

1) Multiplying "Memory Density per I/O" with "Module Data Width" and dividing by 8 for Non-ECC and 9 for ECC modules gives the overall module memory density in MBytes as listed in column "Coding".

**Table 21 DDR2 DRAM Nomenclature**

Field	Description	Values	Coding
1	INFINEON Component Prefix	HYB	Constant
2	Interface Voltage [V]	18	SSTL1.8
3	DRAM Technology	T	DDR2
4	Component Density [Mbit]	256	256 Mbit
		512	512 Mbit
		1G	1 Gbit
		2G	2 Gbit
5+6	Number of I/Os	40	×4
		80	×8
		16	×16
7	Product Variations	0 .. 9	look up table
8	Die Revision	A	First
		B	Second
9	Package, Lead-Free Status	C	FBGA, lead-containing
		F	FBGA, lead-free
10	Speed Grade	-3.7	DDR2-533C
		-5	DDR2-400B
11	N/A for Components		

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